9. The method of claim 8, further including depositing a second encapsulant within the notch.

10. The method of claim 7, further including disposing a second semiconductor die over a second surface of the second substrate opposite the first surface of the second substrate and electrically connected to the first semiconductor die through the first conductive via in the second substrate.

11. The method of claim 7, further including forming a second conductive via through the first semiconductor die.

12. The method of claim 11, further including disposing a second semiconductor die over the first semiconductor die electrically connected to the second conductive via.

13. The method of claim 7, further including:

forming an interconnect structure through the encapsulant over the second substrate; and

electrically connecting the first semiconductor die to the interconnect structure.

~~14. A method of making a semiconductor device, comprising:~~

~~providing a first substrate including a cavity formed in the first substrate;~~

~~providing a second substrate including a conductive via formed through the second substrate;~~

~~disposing the second substrate over the cavity of the first substrate;~~

~~depositing an encapsulant over the first substrate and~~

second substrate; and

disposing a first semiconductor die over a first surface of the second substrate electrically connected to the conductive via.

15. The method of claim 14, further including:

forming a notch in the encapsulant over the second substrate; and

disposing the first semiconductor die within the notch over the first surface of the second substrate.

16. The method of claim 14, further including disposing a second semiconductor die over a second surface of the second substrate opposite the first surface of the second substrate and electrically connected to the first semiconductor die through the conductive via in the second substrate.

17. The method of claim 14, further including:

forming a conductive layer on the first substrate; and

forming a bond wire between the conductive layer and conductive via.

18. The method of claim 14, wherein the second substrate includes a second semiconductor die or interposer.

19. The method of claim 14, further including disposing a second semiconductor die over the first semiconductor die.

20. The method of claim 14, further including forming an interconnect structure over the first substrate.

~~21~~14. A semiconductor device, comprising:

a first substrate including a cavity formed ~~in~~ from a surface of the first substrate through the first substrate;

a second substrate including a conductive via formed through the second substrate, the second substrate being disposed ~~over~~within the cavity of the first substrate;

an encapsulant deposited over the first substrate and second substrate; and

a first semiconductor die disposed over a first surface of the second substrate electrically connected to the conductive via.

~~22~~15. The semiconductor device of claim ~~21~~14, further including a notch formed in the encapsulant over the second substrate, wherein the first semiconductor die is disposed at least partially within the notch over the first surface of the second substrate.

~~23~~16. The semiconductor device of claim ~~21~~14, further including a second semiconductor die disposed over a second surface of the second substrate opposite the first surface of the second substrate and electrically connected to the first semiconductor die through the conductive via in the second substrate.

~~24~~17. The semiconductor device of claim ~~21~~14, further including:

a conductive layer formed on the first substrate; and

a bond wire formed between the conductive layer and conductive via.

~~25~~18. The semiconductor device of claim ~~21~~14, further including a second semiconductor die disposed over the first semiconductor die.